

Notice of References Cited	Application/Control No. 10/540,513		Applicant(s)/Patent Under Reexamination OSADA ET AL.	
	Examiner Eduardo A. Rodela		Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,831,296	11-1998	Kuroda et al.	257/194
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Osamu Ishikawa, Katsunori Nishii, Toshinobu Matsuno, Chinatsu Azuma, Yoshito Ikeda, Syutaro Nanbu and Kaoru Inoue, Low Noise InGaAs HEMT Using the New Off-Set Recess Gate Process, 1989, IEEE MTT-S Digest, Pages 979-982
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.